

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	687	257/440.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/14 13:54
S1	269	silicon\$2on\$2insulator same (photodiode or photodetector or photosensor or (light sensor))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/06 17:27
S2	31	color and S1	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/06 17:02
S3	75745	SOI	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/06 17:02
S4	31290	silicon same S3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 15:28
S5	25362	insulator same S4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/06 17:03
S6	249130	(photodetector or photodiode or photosensor or (light detector) or (light sensor))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/06 17:03

## EAST Search History

S7	250	S5 same S6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/06 17:04
S8	46766	thickness with wavelength	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/06 17:05
S9	3	S7 same S8	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/06 17:05
S10	9	((JOHN) near2 (PETRUZZELLO)). INV.	USPAT	ADJ	OFF	2007/09/06 17:14
S11	8246	silicon-on-insulator	USPAT	ADJ	OFF	2007/09/10 10:05
S12	205	silicon\$2on\$2insulator and spectrometer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/06 18:01
S13	7	silicon\$2on\$2insulator same spectrometer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/06 18:48
S14	2	"5559912".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/06 18:50

## EAST Search History

S15	7	silicon\$2on\$2insulator same spectrometer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 08:52
S16	1	"5726440".PN.	USPAT; USOCR	ADJ	OFF	2007/09/10 09:09
S17	15	("5726440").URPN.	USPAT	ADJ	OFF	2007/09/10 09:11
S18	8246	silicon?on?insulator	USPAT	ADJ	OFF	2007/09/10 10:05
S19	29	S18 same photodiode	USPAT	ADJ	OFF	2007/09/10 10:06
S20	0	"08553972".app.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 10:19
S21	1	"08/553972".app.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 10:19
S22	15	("5726440").URPN.	USPAT	ADJ	OFF	2007/09/10 10:30
S23	4	("5965873").URPN.	USPAT	ADJ	OFF	2007/09/10 10:32
S24	1	"5747840".PN.	USPAT; USOCR	ADJ	OFF	2007/09/10 12:47
S25	0	light same absorption same wavelength same (silicon near1 on near1 insulator)	USPAT; USOCR	ADJ	OFF	2007/09/10 12:48
S26	0	light same absorption same wavelength and (silicon near1 on near1 insulator)	USPAT; USOCR	ADJ	OFF	2007/09/10 12:48
S27	0	light same (absorption or transmission) same layer same wavelength and (silicon near1 on near1 insulator)	USPAT; USOCR	ADJ	OFF	2007/09/10 12:49
S28	0	photon same (absorption or transmission) same layer same wavelength and (silicon near1 on near1 insulator)	USPAT; USOCR	ADJ	ON	2007/09/10 12:52
S29	912	photon same (absorption or transmission) same layer same wavelength	USPAT; USOCR	ADJ	ON	2007/09/10 12:52

## EAST Search History

S30	22	S29 and S18	USPAT; USOCR	ADJ	ON	2007/09/10 12:52
S31	2	"5037781".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 15:28
S32	4	("4673531"   "4681795"   "4682143"   "4693925").PN.	US-PGPUB; USPAT; USOCR	ADJ	OFF	2007/09/10 15:28
S33	0	photodiode and (lateral or horizontal) same burried same (pn junction)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:30
S34	0	photodiode and (lateral or horizontal) same burried same (p n junction)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:30
S35	13	photodiode and (lateral or horizontal) same buried same (p n junction)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:35
S36	0	(silicon substrate) same trench same (lateral) same photodiode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:37
S37	226	buried photodiode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:42

## EAST Search History

S38	726	silicon on insulator	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:37
S39	0	S37 and S38	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:38
S40	14	S37 same trench	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:38
S41	38	forming with (buried photodiode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:44
S42	10	etch\$3 with (buried photodiode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:45
S43	2253	substrate same (lateral or horizontal) same (photodiode or ((pn or (p n)) junction))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:47
S44	726	silicon on insulator	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:47

## EAST Search History

S45	0	S43 and S44	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:47
S46	293	etch\$3 same S43	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 17:00
S47	0	trench same S38	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 16:48
S48	0	(buried diode) same (silicon on insulator)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 17:01
S49	0	(buried diode) and (silicon on insulator)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 17:01
S50	3	(buried diode) same (contact or lead or wire or line) same trench	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 17:01
S51	9935	substrate with (pn junction)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 18:08

## EAST Search History

S52	726	silicon on insulator	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:18
S53	2	S51 and S52	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 18:22
S54	74134	substrate same (diode or photodiode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:18
S55	20	S52 and S54	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 18:26
S56	959	thickness same wavelength same (diode or photodiode) same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 18:27
S57	30	thickness same wavelength same (diode or photodiode) same substrate same (pn junction)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 18:31
S58	0	(filterless with gratingless) same wavelength same thickness same (silicon on insulator)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 18:32

## EAST Search History

S59	0	(filterless with gratingless) and (wavelength same thickness same (silicon on insulator))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 18:32
S60	0	(filterless ) and (wavelength same thickness same (silicon on insulator))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 18:32
S61	0	(filterless with gratingless) same (silicon on insulator)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 18:33
S62	0	(filterless with gratingless) same (silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 18:33
S63	0	filterless same spectrometer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 18:33
S64	2	filterless same photodetector	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 18:33
S65	2	"7233036".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 18:35

## EAST Search History

S66	2	("20030197114"   "6476372").PN.	US-PGPUB; USPAT; USOCR	ADJ	OFF	2007/09/10 18:37
S67	3	pn junction and S52	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:18
S68	19431	silicon?on?insulator	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:19
S69	309	S51 and S68	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:20
S70	38	photodiode and S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:24
S71	24	buried photodiode and S68	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:25
S72	52	S68 same photodiode same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:28

## EAST Search History

S73	76101	substrate same doped same regions same pn same oxide or SOI	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:29
S74	1349	photodiode and S73	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:30
S75	867	S74 and S68	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:30
S76	232	field oxide and S74	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:30
S77	201	field oxide and S75	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:31
S78	42	thickness and wavelength and S77	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:33
S79	46	buried with vertical with (pn junction)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/10 19:34

## EAST Search History

S80	2	"5945722".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/12 18:12
S81	160	257/400.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/13 16:42
S82	2	WO-0037904-\$.DID. OR WO-02099333-\$.DID. OR EP-1152642-\$.DID.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/12 18:16
S83	0	WO-0037904-\$.DID. OR WO-02099333-\$.DID.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/12 18:16
S84	0	WO0037904\$.DID. OR WO02099333\$.DID.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/12 18:16
S85	1	"20030197114".PN.	US-PGPUB	ADJ	OFF	2007/09/12 18:26
S86	1	(buried oxide layer) near5 photodiode near10 substrate	US-PGPUB	ADJ	ON	2007/09/12 18:27
S87	2	(buried oxide layer) same photodiode same p near2 substrate	US-PGPUB	ADJ	ON	2007/09/12 18:27
S88	2	(buried oxide layer) same photodiode same (p near2 substrate)	US-PGPUB	ADJ	ON	2007/09/12 18:28
S89	3	(buried oxide layer) same photodiode same (p near5 substrate)	US-PGPUB	ADJ	ON	2007/09/12 18:30
S90	253	photodiode with (p-type near1 substrate)	US-PGPUB	ADJ	ON	2007/09/12 18:32
S91	4	(buried oxide layer) and S90	US-PGPUB	ADJ	ON	2007/09/12 18:32

## EAST Search History

S92	374	photodiode same (p-type near1 substrate)	US-PGPUB	ADJ	ON	2007/09/12 18:32
S93	5	(buried oxide layer) and S92	US-PGPUB	ADJ	ON	2007/09/12 19:03
S94	3	(buried oxide layer) near5 photodiode	US-PGPUB	ADJ	ON	2007/09/12 19:05
S95	40	((buried oxide layer) or BOX) near5 photodiode	US-PGPUB	ADJ	ON	2007/09/12 19:06
S96	5	((buried oxide) near5 photodiode)	US-PGPUB	ADJ	ON	2007/09/12 19:32
S97	23	((buried oxide) near5 (pn junction))	US-PGPUB	ADJ	ON	2007/09/12 19:11
S98	1676	((oxide) near5 ((pn junction) or diode or photodiode))	US-PGPUB	ADJ	ON	2007/09/12 19:11
S99	47	((buried oxide) near5 ((pn junction) or diode or photodiode))	US-PGPUB	ADJ	ON	2007/09/12 19:14
S10 0	0	((pn junction) or (diode)) on (buried oxide)	US-PGPUB	ADJ	ON	2007/09/12 19:32
S10 1	0	((pn junction) or (diode)) near2 on near2 (buried oxide)	US-PGPUB	ADJ	ON	2007/09/12 19:32
S10 2	8	(p-type substrate) near3 (n-type near2 region near3 buried)	US-PGPUB	ADJ	ON	2007/09/12 19:34
S10 3	0	(n-type substrate) near3 (p-type near2 region near3 buried)	US-PGPUB	ADJ	ON	2007/09/12 19:34
S10 4	11	(n-type substrate) near3 (p-type near4 buried)	US-PGPUB	ADJ	ON	2007/09/12 19:35
S10 5	27	((n-type or p-type) substrate) near3 ((p-type or n-type) near4 buried)	US-PGPUB	ADJ	ON	2007/09/12 19:35
S10 6	3	oxide same S105	US-PGPUB	ADJ	ON	2007/09/12 20:23
S10 7	0	"65071549".pn.	US-PGPUB	ADJ	ON	2007/09/12 20:23
S10 8	0	"6507159".pn.	US-PGPUB	ADJ	ON	2007/09/12 20:23
S10 9	0	"6507159".pn.	US-PGPUB	ADJ	ON	2007/09/12 20:23
S11 0	1	("6507159").PN.	US-PGPUB; USPAT	OR	OFF	2007/09/12 20:23
S11 1	687	257/440.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/13 16:42

## EAST Search History

S11 2	219	S111 and oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/13 17:05
S11 3	1499	257/431	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/13 17:05
S11 4	1675	257/431.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/13 17:05
S11 5	672	S114 and oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/13 18:23
S11 6	13	S114 and (buried oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/13 17:05
S11 7	189	S114 and (oxide layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/13 17:38
S11 8	330	("buried oxide").ti.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/13 18:23

## EAST Search History

S11 9	142	("buried oxide layer").ti.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/13 18:24
S12 0	330	("buried oxide").ti:	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/13 18:24
S12 1	15	("buried oxide layer").ti.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	ADJ	OFF	2007/09/13 18:24
S12 2	91	("buried oxide").ti.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	ADJ	OFF	2007/09/13 18:51
S12 3	1090	(contact or lead or wire or electrode) with (buried near2 (diode or photodiode or transistor or phototransistor or element))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	ADJ	OFF	2007/09/13 18:53
S12 4	440	(contact or lead or wire or electrode) near3 (buried near2 (diode or photodiode or transistor or phototransistor or element))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	ADJ	OFF	2007/09/13 18:53
S12 5	364	(contact or lead or wire or electrode) near2 (buried near2 (diode or photodiode or transistor or phototransistor or element))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	ADJ	OFF	2007/09/13 18:53
S12 6	39	(contact or lead or wire or electrode) near2 (buried near2 (diode or photodiode or transistor or phototransistor or element)) same trench	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	ADJ	OFF	2007/09/13 18:53

## EAST Search History

S12 7	2	"6507159".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/09/13 19:56
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